SKiiP 12NAB12T4V1



MiniSKiiP[®] 1

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 12NAB12T4V1

Target Data

Features

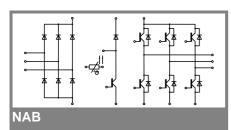
- Latest Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 10 kVA
- Typical motor power 5,5 kW

Remarks

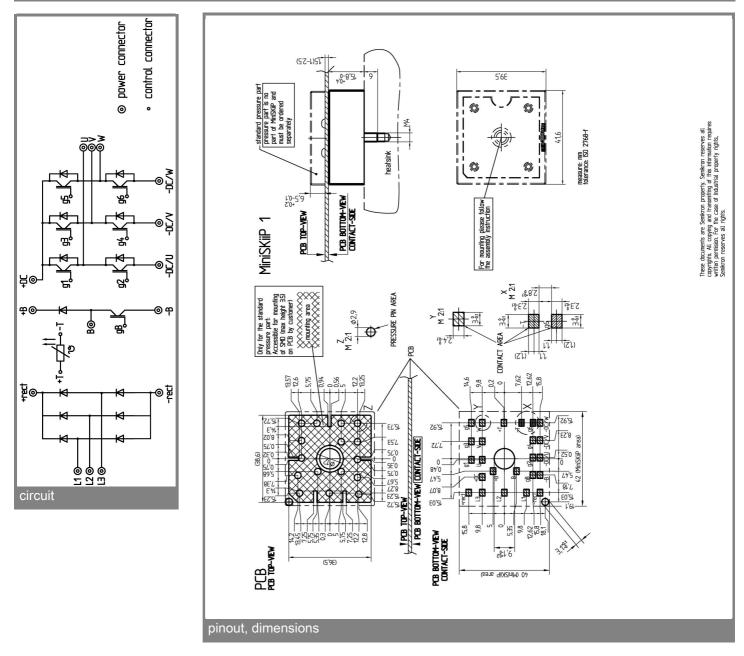
• V_{CEsat}, V_F = chip level value



Absolute	Maximum Ratings	$T_s = 25 \text{ °C}$, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V _{CES}		1200	V				
I _C	T _s = 25 (70) °C	18 (18)	А				
I _{CRM}	$t_p \le 1 \text{ ms}$	45	А				
V _{GES}		± 20	V				
Т _ј		- 40 + 175	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C	22 (18)	А				
I _{FRM}	$t_p \le 1 ms$	45	А				
Т _ј		- 40 + 175	°C				
Diode - Rectifier							
V _{RRM}		1600	V				
I _F	T _s = 70 °C	35	А				
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	220	А				
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A²s				
Т _ј		- 40 + 150	°C				
I _{tRMS}	per power terminal (20 A / spring)	20	Α				
T _{stg}	$T_{op} \leq T_{stg}$	- 40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

Characteristics T _s = 25 °C, unless otherwise specie								
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V _{CEsat}	I _{Cnom} = 15 A, T _j = 25 (150) °C		1,85 (2,25)	2,05 (2,45)	V			
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = mA$	5	5,8	6,5	V			
V _{CE(TO)}	T _i = 25 (150) °C		1,1 (1)	1,3 (1,2)	V			
r _T	$T_{i} = 25 (150) \ ^{\circ}C$		50 (83)	50 (83)	mΩ			
Cies	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		-		nF			
C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		-		nF			
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		-		nF			
R _{th(j-s)}	per IGBT		1,22		K/W			
t _{d(on)}	under following conditions		12		ns			
t, Ó	V _{CC} = 600 V, V _{GE} = ± 15 V		24		ns			
t _{d(off)}	I _{Cnom} = 15 A, T _i = 150°C		256		ns			
t _f	$R_{Gon} = R_{Goff} = -\Omega$		74		ns			
Eon	inductive load		1,4		mJ			
E _{off}			1,3		mJ			
Diode - In	verter, Chopper	•						
V _F = V _{EC}	I _{Fnom} = 15 A, T _i = 25 (150) °C		2,4 (2,45)	2,75 (2,8)	V			
V _(TO)	$T_i = 25 (150) °C$		1,3 (0,9)	1,5 (1,1)	V			
r _T	T _i = 25 (150) °C		73 (103)	83 (113)	mΩ			
R _{th(j-s)}	per diode		2,02		K/W			
I _{RRM}	under following conditions		28		Α			
Q _{rr}	I _{Enom} = 15 A, V _R = 600 V		2,6		μC			
E _{rr}	$V_{GE} = 0 V, T_{i} = 150 °C$		1,1		mJ			
	di _F /dt = - A/µs							
Diode - R	ectifier				1			
V _F	I _{Fnom} = 15 A, T _i = 25 °C	1	1,1		V			
V _(TO)	$T_{i} = 150 \ ^{\circ}C$		0,8		V			
r _T	T _i = 150 °C		20		mΩ			
R _{th(j-s)}	per diode		1,5		K/W			
	ure Sensor	1			1			
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω			
Mechanic		1			1			
w			35		g			
Ms	Mounting torque	2		2,5	Nm			

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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